



STW42N65M5 Information



For Reference Only

Part Number STW42N65M5

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 33A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STW42N65M5 Specifications

Manufacturer Part Number STW42N65M5 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series MDmesh? V FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 33A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4650pF @ 100V Vgs (Max) ±25 V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series MDmesh? V FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 33A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4650pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Manufacturer Part Number	STW42N65M5
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SeriesMDmesh? VFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C33A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4650pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C33A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4650pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Series	MDmesh? V
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C33A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4650pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250μA Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±25V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 33A (Tc) 34A (Tc) 54C (14C) 34A (Tc) 34A (Tc) 54C (Ti) 46S (Pi 10V 46S (Pi 10	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4650pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Supplier Device Package TO-247-3 Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	33A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4650pF @ 100V Vgs (Max) ±25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	100nC @ 10V
FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	4650pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Power Dissipation (Max)	190W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	79 mOhm @ 16.5A, 10V
Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

STW42N65M5 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STW42N65M5 Payment Methods



















STW42N65M5 Shipping Methods













If you have any question about STW42N65M5, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com